



□ Assume only 1 atom high "defects" on each surrounding silicon layer

For a modern "scaled" oxide, ~5-6 atoms thick, 33% variability is induced

□ The <u>bad news</u>

Single atom defects can cause local current leakage 10-100x higher than average

□ The <u>really bad news</u>

Such "non-statistical behaviors" are appearing elsewhere in technology
Unless you're a company driving frontier of device & circuit simulation

B. Meyerson